TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIII)

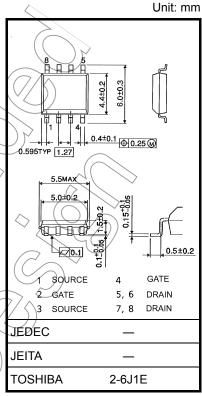
TPC8208

Lithium Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON resistance: $RDS(ON) = 38 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 6.3 \text{ S (typ.)}$
- Low leakage current: $IDSS = 10 \mu A (max) (VDS = 20 V)$
- Enhancement mode: V_{th} = 0.5 to 1.2 V (V_{DS} = 10 V, I_{D} = 200 μA) \langle

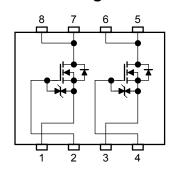
Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	20(> V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	20	V
Gate-source voltage		V _{GSS}	±12	V
Drain current	DC (Note 1)	I _D	5	A
	Pulse (Note 1)	I _{DP}	20	<\A
Drain power dissipation (t = 10 s) (Note 2a)	Single-device operation (Note 3a)	P _D (1)	1.5	
	Single-device value at dual operation (Note 3b)	R _D (2)	1.1	w N
Drain power dissipation (t = 10 s) (Note 2b)	Single-device operation (Note 3a)	PD (1)	0.75	
	Single-device value at dual operation (Note 3b)	P _{D (2)}	0.45	W
Single pulse avalanche energy (Note 4)		EAS	16.3	mJ
Avalanche current		IAR	√ 5	Α
Repetitive avalanche energy Single-device value at dual operation (Note 2a, 3b, 5)		EAR	0.1	mJ
Channel temperature		Toh	150	°C
Storage tempera	ture range	Jstg	-55 to 150	°C



Weight: 0.080 g (typ.)

Circuit Configuration



Note: Note 1, Note 2, Note 3, Note 4 and Note 5: See the next page.

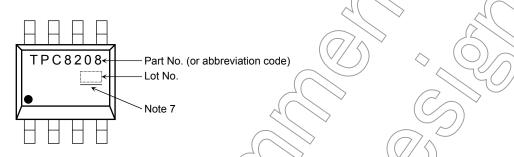
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Please handle with caution.

Thermal Characteristics

Characteristics	Symbol	Max	Unit	
The second resistance of a great to english	Single-device operation (Note 3a)	R _{th (ch-a) (1)}	83.3	
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	Single-device value at dual operation (Note 3b)	R _{th} (ch-a) (2)	114	°C/W
Thermal resistance, shannel to embient	Single-device operation (Note 3a)	R _{th (ch-a) (1)}	167	
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	Single-device value at dual operation (Note 3b)	R _{th (ch-a) (2)}	278	°C/W

Marking (Note 6)



Note 1: Ensure that the channel temperature does not exceed 150°C

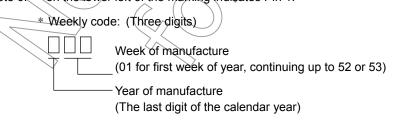
Note 2: a) Device mounted on a glass-epoxy board (a)

b) Device mounted on a glass-epoxy board (b)



- Note 3: a) The power dissipation and thermal resistance values are shown for a single device. (During single-device operation, power is only applied to one device.)
 - b) The power dissipation and thermal resistance values are shown for a single device. (During dual operation, power is evenly applied to both devices.)
- Note 4: $V_{DD} = 16 \text{ V}$, $T_{Ch} = 25 \text{ C}$ (initial), L = 0.5 mH, $R_G = 25 \Omega$, $I_{AR} = 5 \text{ A}$
- Note 5: Repetitive rating:pulse width limited by maximum channel temperature

Note 6: • on the lower left of the marking indicates Pin 1.



Note 7: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

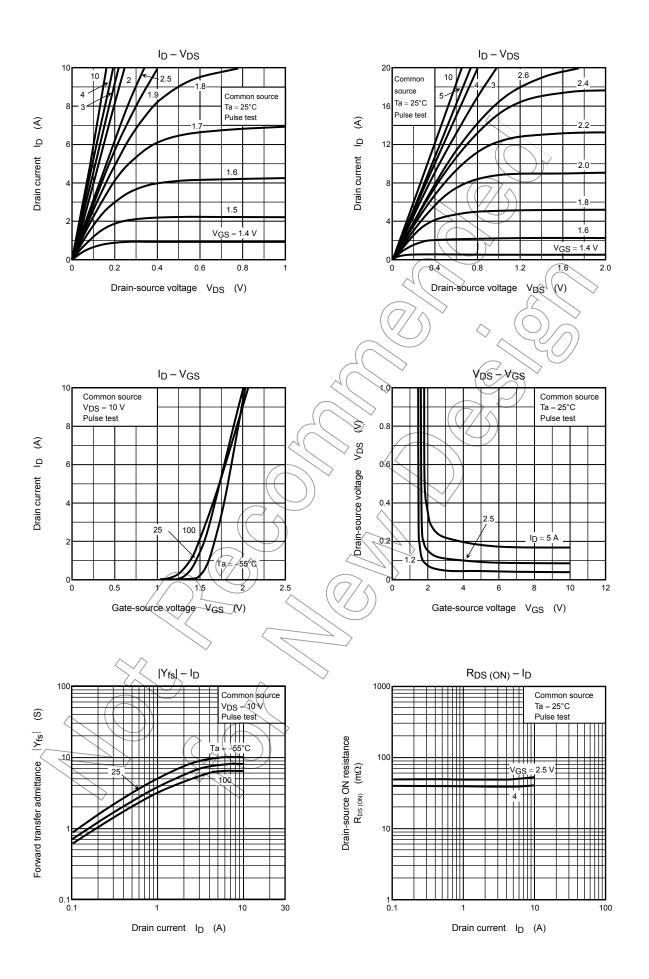
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Electrical Characteristics (Ta = 25°C)

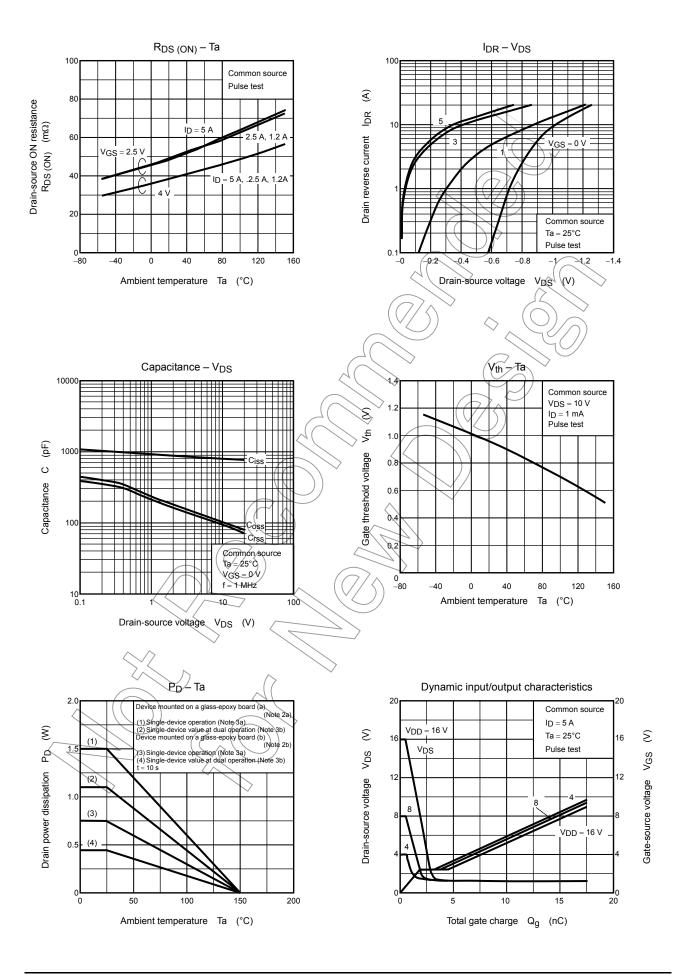
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cut-OFF cu	rrent	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V	_	_	10	μА
Drain-source breakdown voltage		V _{(BR)DSS}	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	20	_		>
		V _{(BR)DSX}	$I_D = 10 \text{ mA}, V_{GS} = -12 \text{ V}$	8	_	_	V
Gate threshold vo	oltage	V _{th}	$V_{DS} = 10 \text{ V}, I_D = 200 \mu\text{A}$	0.5) <u>}_</u>	1.2	V
	Drain-source ON resistance		$V_{GS} = 2.0 \text{ V}, I_D = 2.5 \text{ A}$		57	100	
Drain-source ON			V _{GS} = 2.5 V, I _D = 2.5 A	\rightarrow	46	70	mΩ
			V _{GS} = 4.0 V, I _D = 2.5 A	\	38	50	
Forward transfer admittance		Y _{fs}	V _{DS} = 10 V, I _D = 2.5 A	3.2	6.3		S
Input capacitance	Input capacitance			_	780		
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		90	/	pF
Output capacitan	Output capacitance				100	> —	
	Rise time	t _r	ID = 2.5 A		5.0) —	
Switching time	Turn-ON time	t _{on}	VGS 5 V ID = 2.5 A	76	> 12	_	ns
	Fall time	t _f	27 4 W W 8 4 7 7 8 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9 9		2.7		115
	Turn-OFF time	t _{off}	V _{DD} ≥ 10 V Duty ≨ 1%, t _w = 10 μs		21		
Total gate charge (gate-source plus gate-drain)		Qg			9.5		
Gate-source charge 1		Q _{gs1}	$V_{DD} \simeq 16 \text{ V}, V_{GS} = 5 \text{ V}, V_{D} \neq 5 \text{ A}$	_	2.0	_	nC
Gate-drain ("miller") charge		Qgd		_	2.2	_	

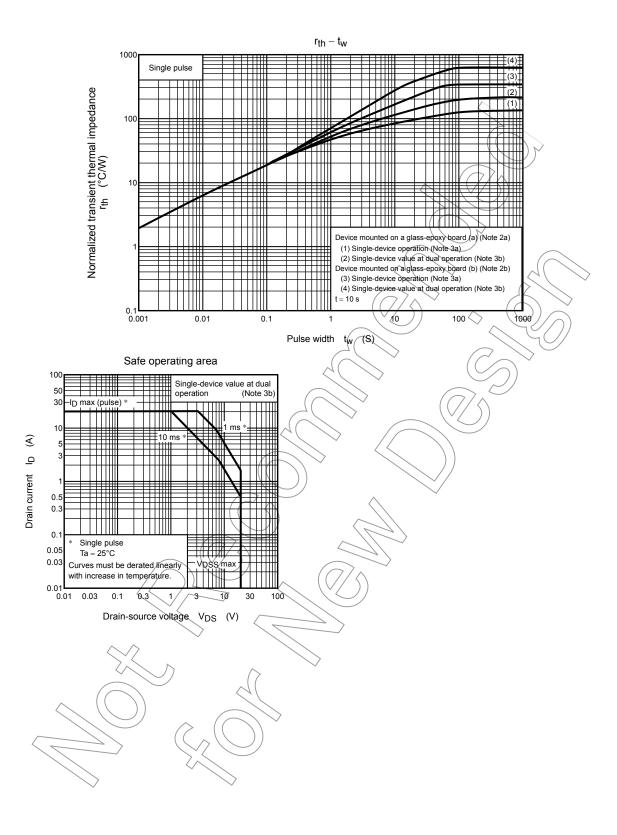
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristi	cs	Symbol Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	IDRP —	_	_	20	Α
Forward voltage (diode)	\Diamond	V_{DSF} $I_{DR} = 5 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.2	V



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